

# HESD8704MUTAG ESD PROTECTION DIODE

### Discription

The HESD8704MUTAG is a 4-channel ultra low capacitance rail clam ESD protection diodes array . Each channel consists of a pair of diodes that steer positive or negative ESD current to either the positive or negative rail . A zener diode is integrated in to the array between the positive and negative supply rails. In the typical applications, the negative rail pin (assigned as GND) is connected with system ground . The Positive ESD current is steered to the ground through an ESD diode and Zener diode and the positive ESD voltage is clamped to the zener voltage.

#### Features

- $\star$  4 channels of ESD protection;
- ★ Provides ESD protection to IEC61000-4-2 level 4 - ±15kV air discharge
  - ±10kV contact discharge;
- ★ Channel I/O to GND capacitance: 0.55pF (Max)
- ★ Channel I/O to I/O capacitance: 0.6pF (Max)
- ★ Low clamping voltage;
- ★ Low operating voltage;
- ★ Improved zener structure;
- ★ Optimized package for easy high speed data lines PCB layout;
- ★ RoHS compliant and Halogen Free.

# Orderingin formation

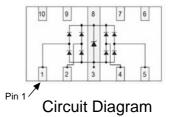
Product ID	Pack	Qty(PCS)
HESD8704MUTAG	DFN2510-10L	3000

#### Absolute Ratings(Tamb = 25°C)

Symbol	Parameter	Value	Units
P <sub>PP</sub>	Peak Pulse Power (t <sub>P</sub> = 8/20µs)	70	W
IPP	Peak Pulse Current(8/20us)	4	А
TL	Maximum lead temperature for soldering during 10s		°C
T <sub>stg</sub>	Storage Temperature Range	-55 to +150	°C
T <sub>op</sub>	Operating Temperature Range	-40 to +125	°C
Tj	Maximum junction temperature		°C
	IEC61000-4-2 (ESD) air discharge contact discharge	±15 ±10	KV



DFN2510-10L

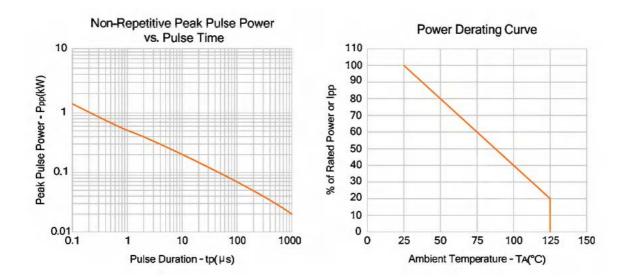


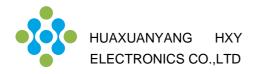


## Electrical Characteristics (Ta= 25°C)

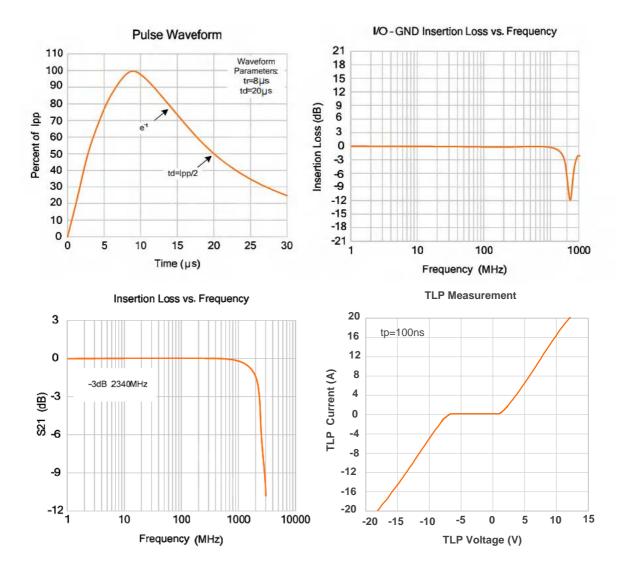
Symbol	Parameter	Test Condition	Min	Тур	Max	Units
Vrwm	Reverse Working Voltage				3.3	V
V <sub>br</sub>	Reverse Breakdown Voltage	l⊤ = 1mA	5.6			V
IR	Reverse Leakage Current	V <sub>RWM</sub> = 5.0V			1.0	μA
Vc	Clamping Voltage	$I_{RWM} = 1A, t_p = 8/20 \mu s$		7		V
vc	Clamping Voltage	$I_{RWM} = 4A, t_p = 8/20 \mu s$		8	20	V
CJ	Junction Capacitance	$V_R = 0V$ , f = 1MHz Any I/O pin to GND		0.5	0.6	pF
CJ	Junction Capacitance	$V_R = 0V$ , f = 1MHz Any I/O pin to I/O		0.3	0.4	pF

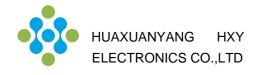
# **Typical Characteristics**



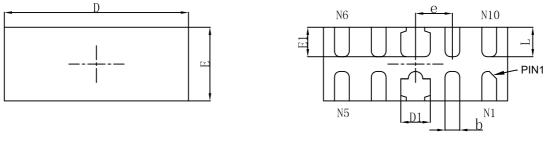


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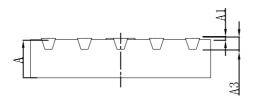




## **Outline And Dimensions**



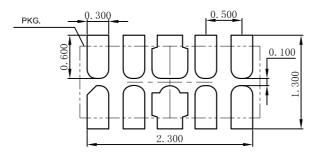
**Bottom View** 



# Side View

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
А	0.450	0.550	0.017	0.022
A1	0.000	0.050	0.000	0.002
A3	0.152REF.		0.006REF.	
D	2.450	2.550	0.096	0.100
Е	0.950	1.050	0.037	0.041
D1	0.350	0.450	0.014	0.018
E1	0.350	0.450	0.014	0.018
b	0.150	0.250	0.006	0.010
е	0.500TYP.		0.020TYP.	
L				

# **Soledering Footprint**





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